



DMN5L06T

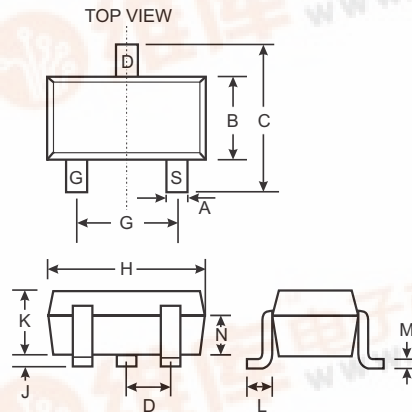
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

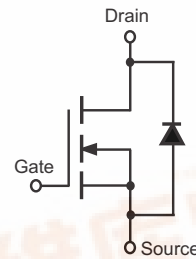
- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking: Date Code and Type Code, See Page 2
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
All Dimensions in mm			



EQUIVALENT CIRCUIT

Maximum Ratings @ T_A = 25°C unless otherwise specified

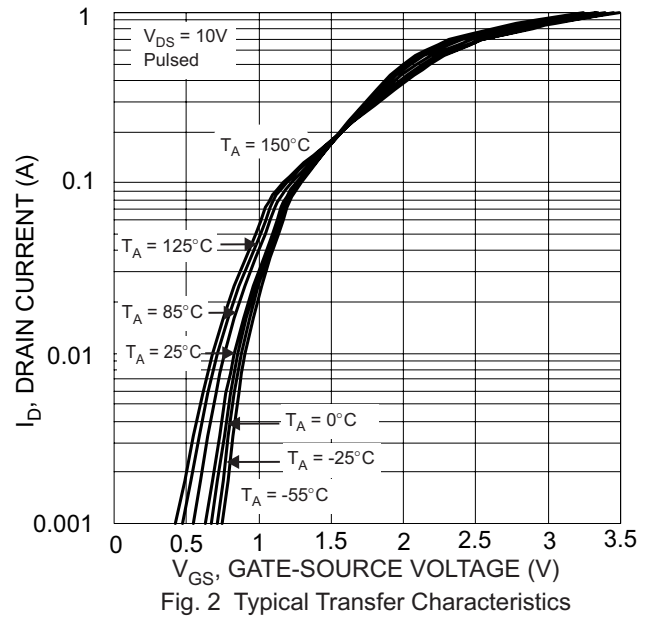
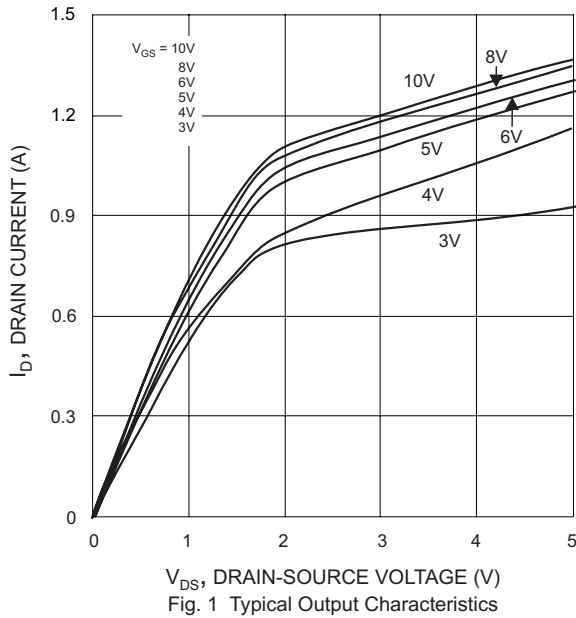
Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DS}	50	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	50	V
Gate-Source Voltage	V _{GS}	±20 ±40	V
Drain Current (Note 1)	I _D	280	mA
Drain Current (Note 1)	I _{DM}	1.5	A
Total Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics

 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.1 1 500	μA	$@ T_C = 25^\circ\text{C}$ $@ T_A = 85^\circ\text{C}$ $@ T_C = 125^\circ\text{C}$ $V_{DS} = 50V, V_{GS} = 0V$ $V_{DS} = 20V, V_{GS} = 0V$ $V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 20 ± 1	nA μA	$@ T_A = 25^\circ\text{C}$ $@ T_A = 85^\circ\text{C}$ $V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	0.49	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.6 2.2	3 4	Ω	$V_{GS} = 2.7V, I_D = 0.2A$ $V_{GS} = 1.8V, I_D = 50mA$
On-State Drain Current	$I_{D(on)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage	V_{SD}	0.5	—	1.4	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	



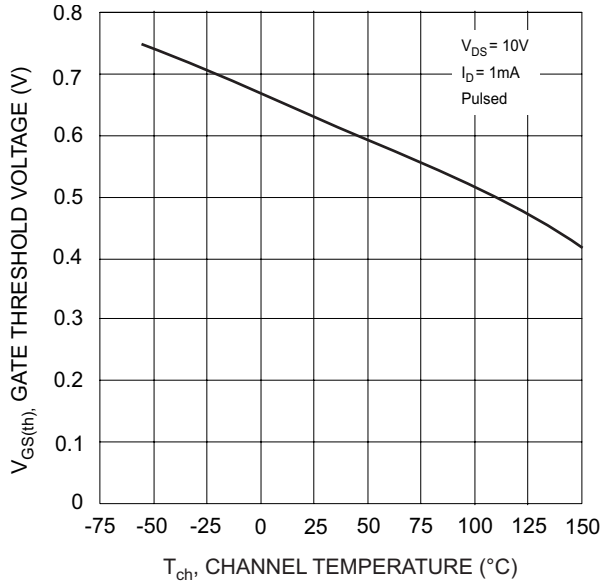


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

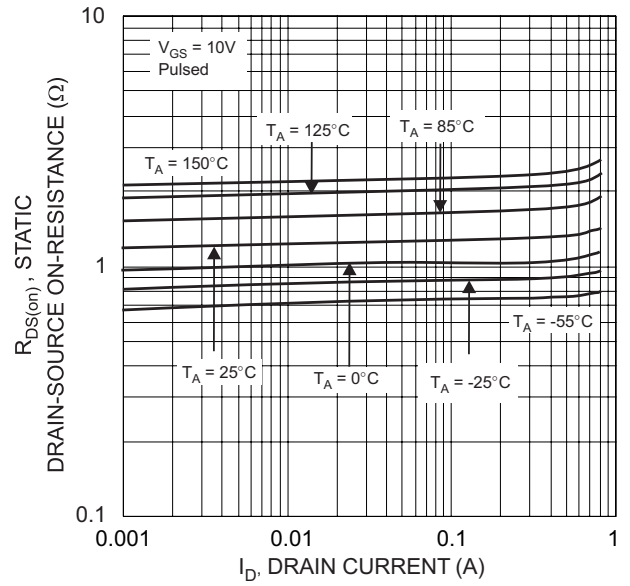


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

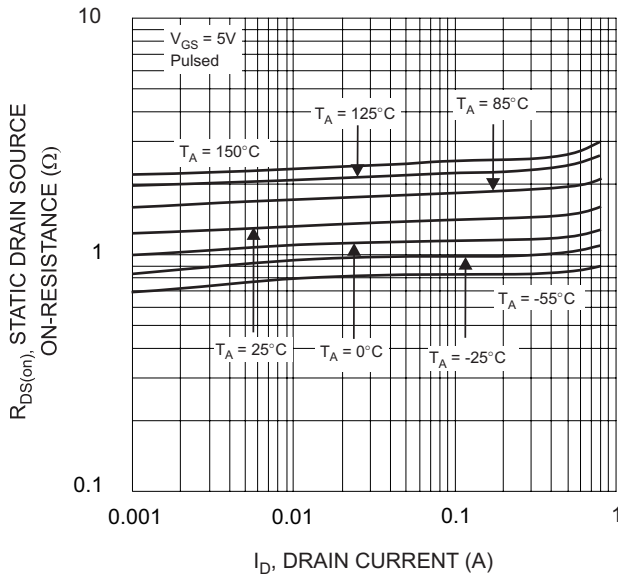


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

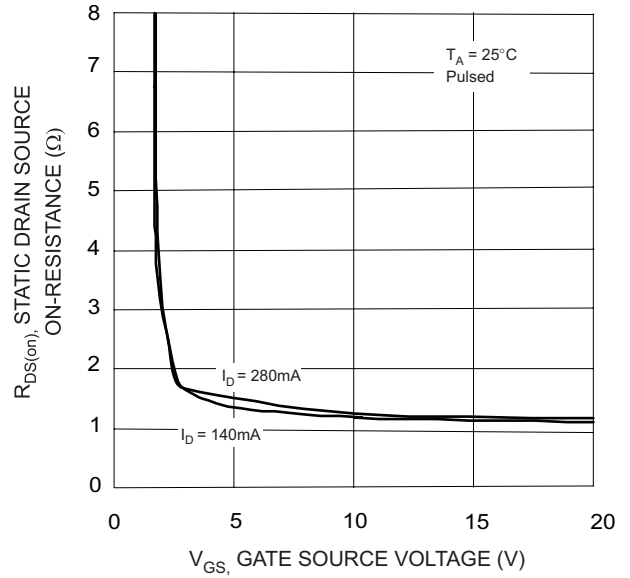


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

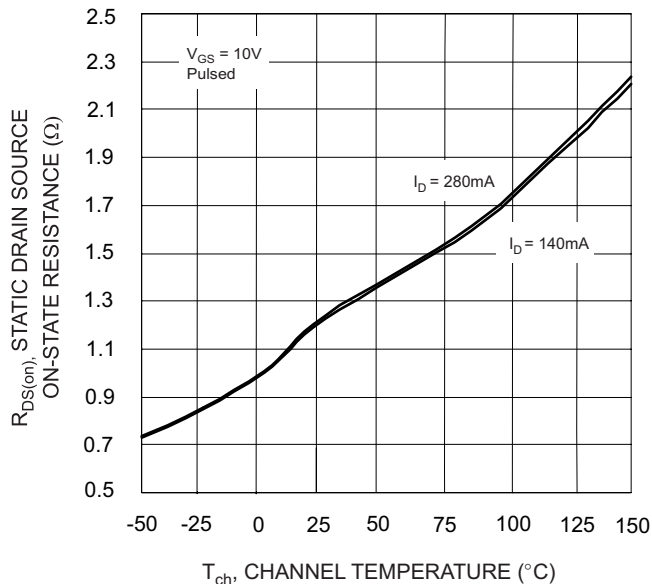


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

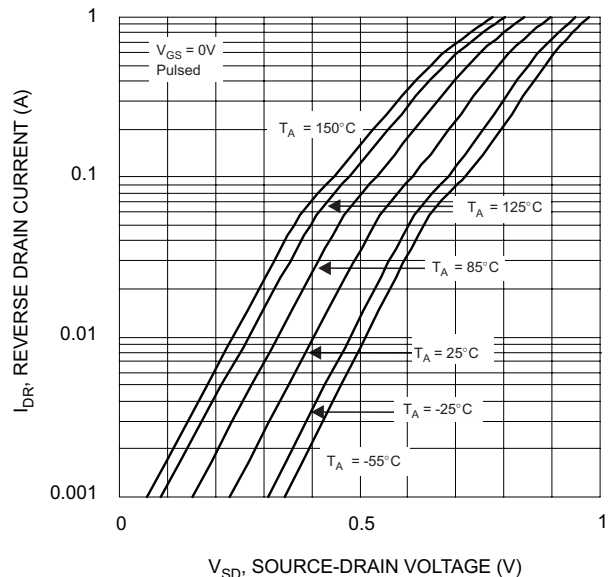


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

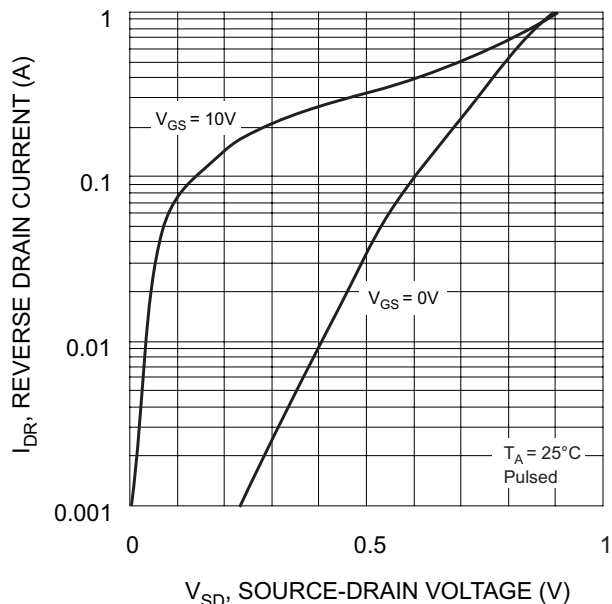


Fig. 9 Reverse Drain Current
vs. Source-Drain Voltage

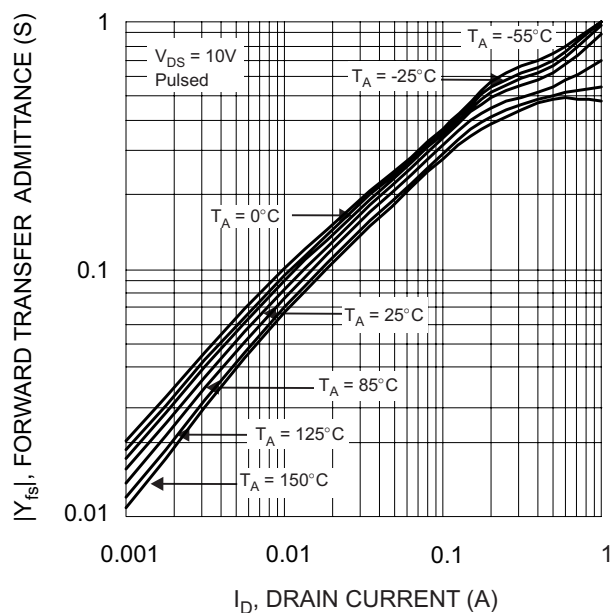


Fig. 10 Forward Transfer Admittance
vs. Drain Current

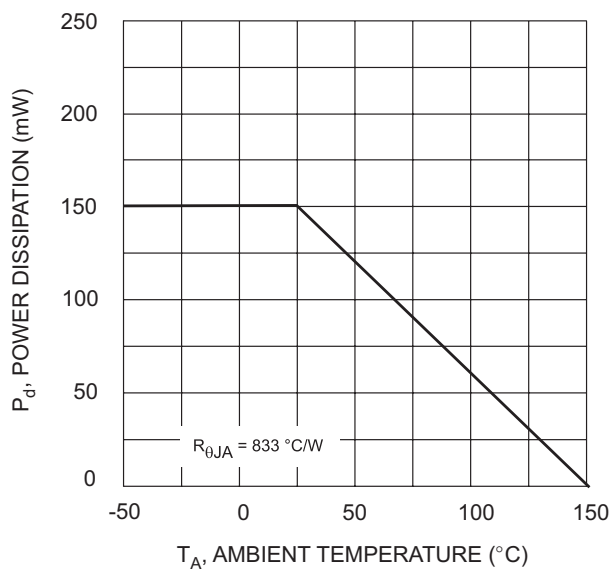


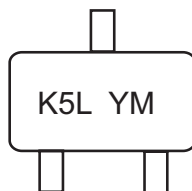
Fig. 11, Derating Curve - Total

Ordering Information (Note 5)

Device	Packaging	Shipping
DMN5L06T-7	SOT-523	3000/Tape & Reel

- Notes:
- Short duration test pulse used to minimize self-heating effect.
 - For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K5L = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: S = 2005
M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009
Code	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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